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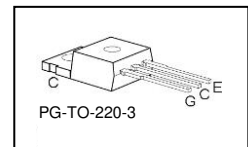
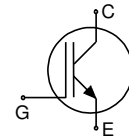


Low Loss IGBT : IGBT in TRENCHSTOP™ and Fieldstop technology



### Features:

- Very low  $V_{CE(sat)}$  1.5V (typ.)
- Maximum Junction Temperature 175°C
- Short circuit withstand time 5 $\mu$ s
- Designed for :
  - Variable Speed Drive for washing machines and air conditioners
  - induction cooking
  - Uninterrupted Power Supply
- TRENCHSTOP™ and Fieldstop technology for 600V applications offers :
  - very tight parameter distribution
  - high ruggedness, temperature stable behaviour
- NPT technology offers easy parallel switching capability due to positive temperature coefficient in  $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Qualified according to JEDEC<sup>1</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	$V_{CE}$	$I_C$	$V_{CE(sat), T_j=25^\circ C}$	$T_{j,max}$	Marking Code	Package
IGP10N60T	600V	10A	1.5V	175°C	G10T60	PG-TO-220-3

### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j \geq 25^\circ C$	$V_{CE}$	600	V
DC collector current, limited by $T_{j,max}$	$I_C$	24	A
$T_C = 25^\circ C$		18	
$T_C = 100^\circ C$			
Pulsed collector current, $t_p$ limited by $T_{j,max}$	$I_{C,puls}$	30	
Turn off safe operating area, $V_{CE} = 600V$ , $T_j = 175^\circ C$ , $t_p = 1\mu s$	-	30	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Short circuit withstand time <sup>2)</sup>	$t_{SC}$	5	$\mu s$
$V_{GE} = 15V$ , $V_{CC} \leq 400V$ , $T_j \leq 150^\circ C$			
Power dissipation $T_C = 25^\circ C$	$P_{tot}$	110	W
Operating junction temperature	$T_j$	-40...+175	°C
Storage temperature	$T_{stg}$	-55...+150	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s		260	

<sup>1</sup> J-STD-020 and JESD-022

<sup>2)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

### Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		1.35	K/W
Thermal resistance, junction – ambient	$R_{thJA}$		62	

### Electrical Characteristic, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit	
			min.	typ.	max.		
<b>Static Characteristic</b>							
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.2mA$	600	-	-	V	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=10A$	-	1.5	2.05		
		$T_j=25\text{ °C}$	-	1.8	-		
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=0.3mA, V_{CE}=V_{GE}$	4.1	4.6	5.7		
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=600V, V_{GE}=0V$	$T_j=25\text{ °C}$	-	-	40	$\mu A$
			$T_j=175\text{ °C}$	-	-	1000	
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA	
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=10A$	-	6	-	S	
Integrated gate resistor	$R_{Gint}$		none			$\Omega$	

### Dynamic Characteristic

Input capacitance	$C_{iss}$	$V_{CE}=25V, V_{GE}=0V, f=1MHz$	-	551	-	$\mu F$
Output capacitance	$C_{oss}$		-	40	-	
Reverse transfer capacitance	$C_{rss}$		-	17	-	
Gate charge	$Q_{Gate}$	$V_{CC}=480V, I_C=10A, V_{GE}=15V$	-	62	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$	TO-220-3-1	-	7	-	nH
Short circuit collector current <sup>1)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 5\mu s, V_{CC}=400V, T_j=25\text{ °C}$	-	100	-	A

<sup>1)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

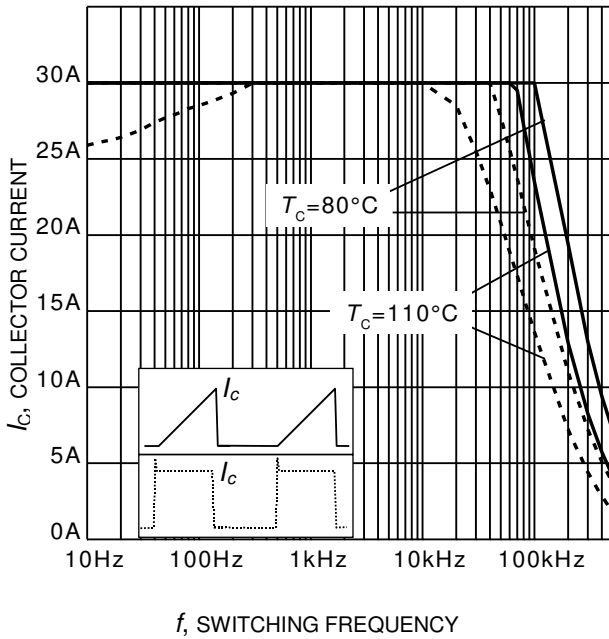
### Switching Characteristic <sup>3)</sup>, Inductive Load, at $T_j=25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25\text{ °C}$ , $V_{CC}=400\text{ V}$ , $I_C=10\text{ A}$ , $V_{GE}=0/15\text{ V}$ , $r_G=23\text{ }\Omega$ , $L_\sigma=60\text{ nH}$ , $C_\sigma=40\text{ pF}$	-	12	-	ns
Rise time	$t_r$		-	8	-	
Turn-off delay time	$t_{d(off)}$		-	215	-	
Fall time	$t_f$		-	38	-	
Turn-on energy	$E_{on}$	$L_\sigma$ , $C_\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. Diode from IKP10N60T	-	0.16	-	mJ
Turn-off energy	$E_{off}$		-	0.27	-	
Total switching energy	$E_{ts}$		-	0.43	-	

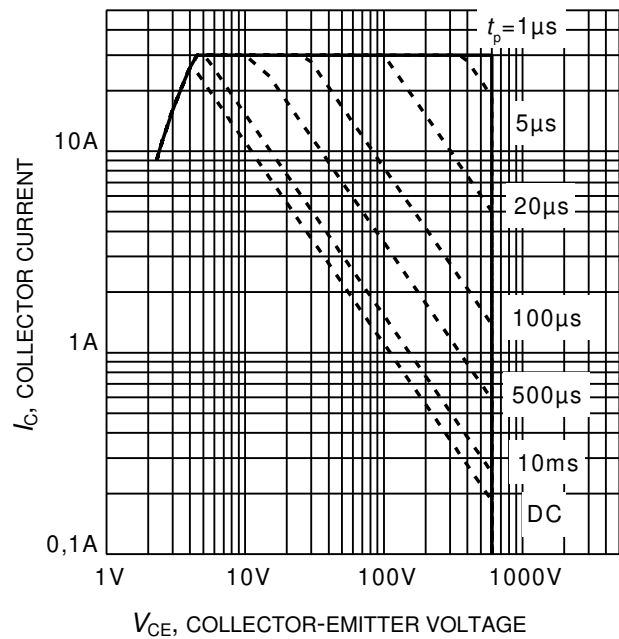
### Switching Characteristic <sup>3)</sup>, Inductive Load, at $T_j=175\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=175\text{ °C}$ , $V_{CC}=400\text{ V}$ , $I_C=10\text{ A}$ , $V_{GE}=0/15\text{ V}$ , $r_G=23\text{ }\Omega$ , $L_\sigma=60\text{ nH}$ , $C_\sigma=40\text{ pF}$	-	10	-	ns
Rise time	$t_r$		-	11	-	
Turn-off delay time	$t_{d(off)}$		-	233	-	
Fall time	$t_f$		-	63	-	
Turn-on energy	$E_{on}$	$L_\sigma$ , $C_\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. Diode from IKP10N60T	-	0.26	-	mJ
Turn-off energy	$E_{off}$		-	0.35	-	
Total switching energy	$E_{ts}$		-	0.61	-	

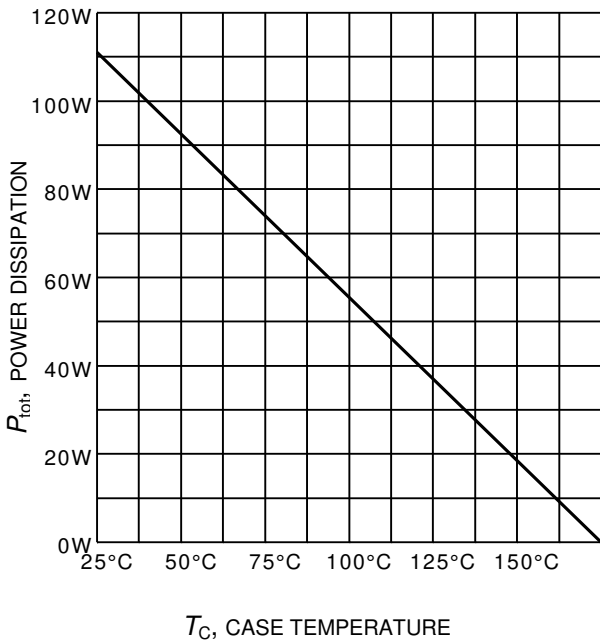




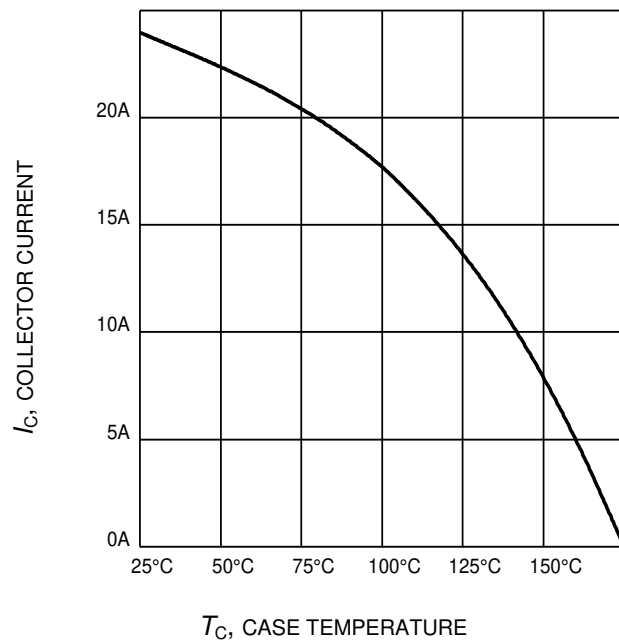
**Figure 1. Collector current as a function of switching frequency**  
 ( $T_j \leq 175^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $r_G = 23\Omega$ )



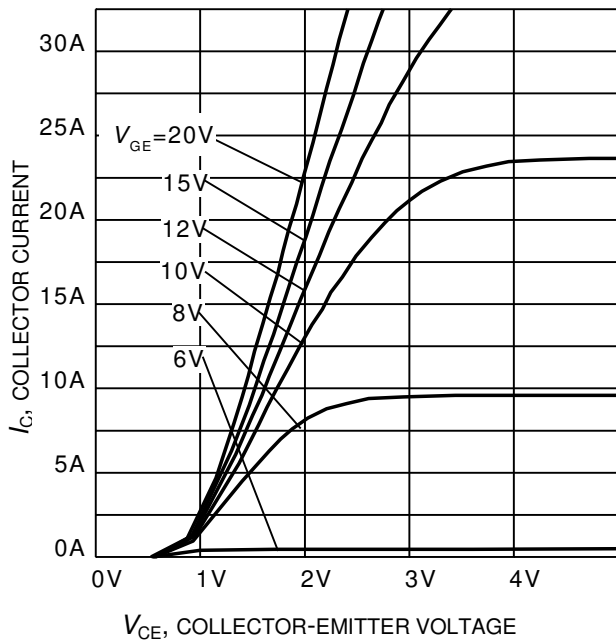
**Figure 2. Safe operating area**  
 ( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 175^\circ\text{C}$ ;  $V_{GE} = 0/15\text{V}$ )



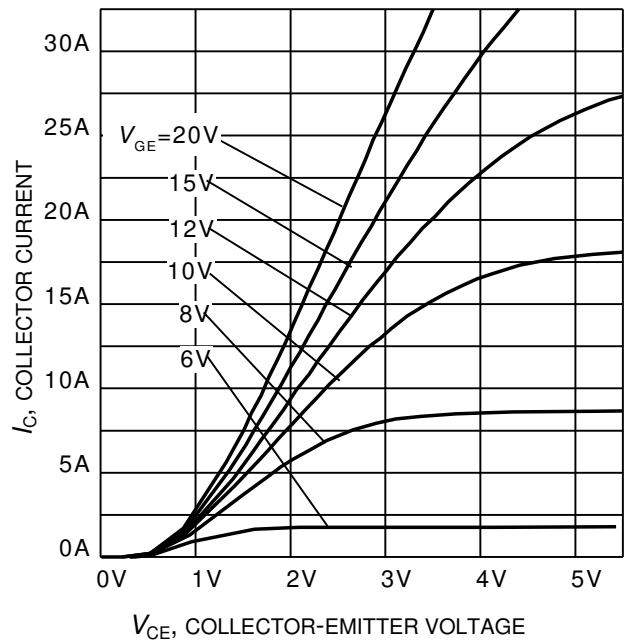
**Figure 3. Power dissipation as a function of case temperature**  
 ( $T_j \leq 175^\circ\text{C}$ )



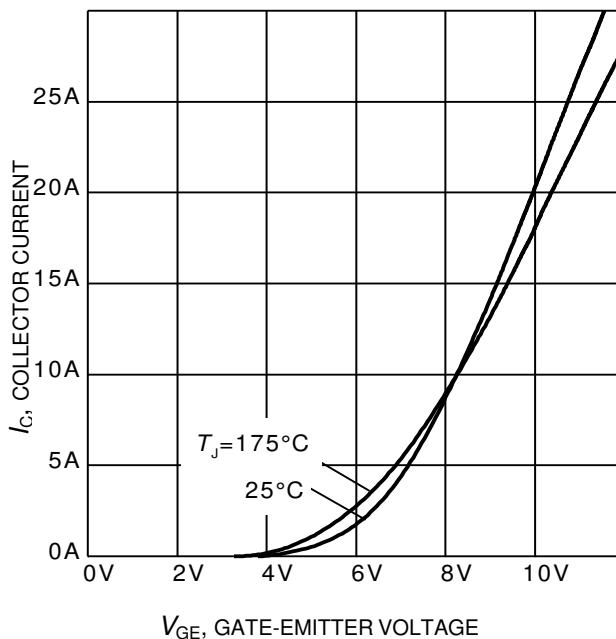
**Figure 4. Collector current as a function of case temperature**  
 ( $V_{GE} \geq 15\text{V}$ ,  $T_j \leq 175^\circ\text{C}$ )



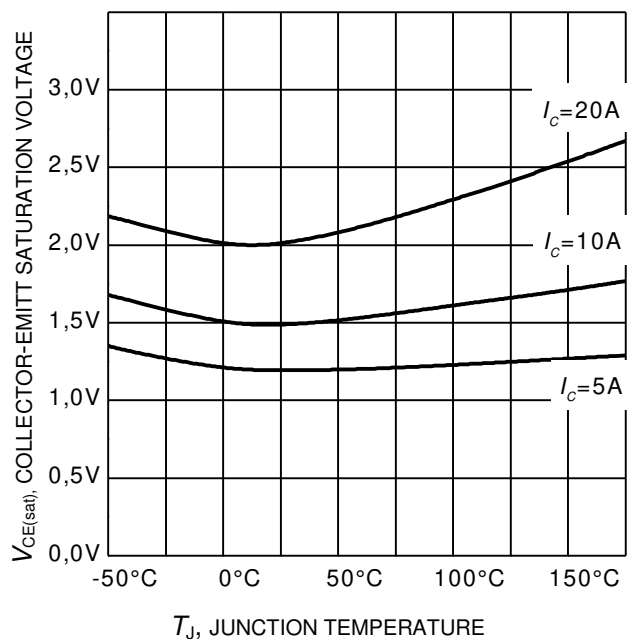
**Figure 5. Typical output characteristic**  
( $T_j = 25^\circ\text{C}$ )



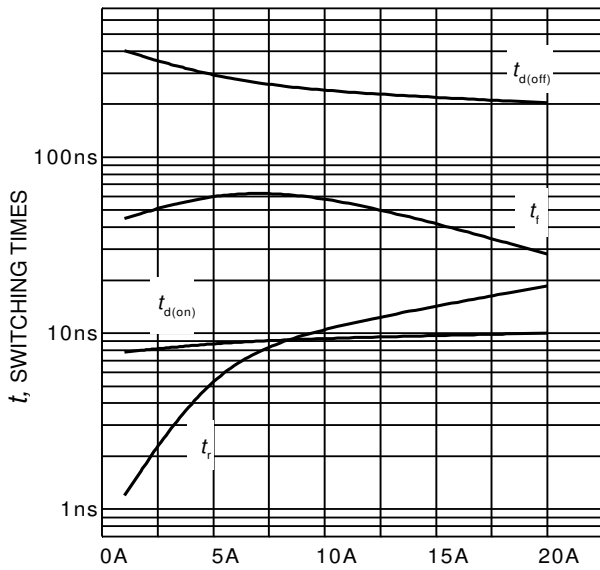
**Figure 6. Typical output characteristic**  
( $T_j = 175^\circ\text{C}$ )



**Figure 7. Typical transfer characteristic**  
( $V_{CE} = 20\text{V}$ )

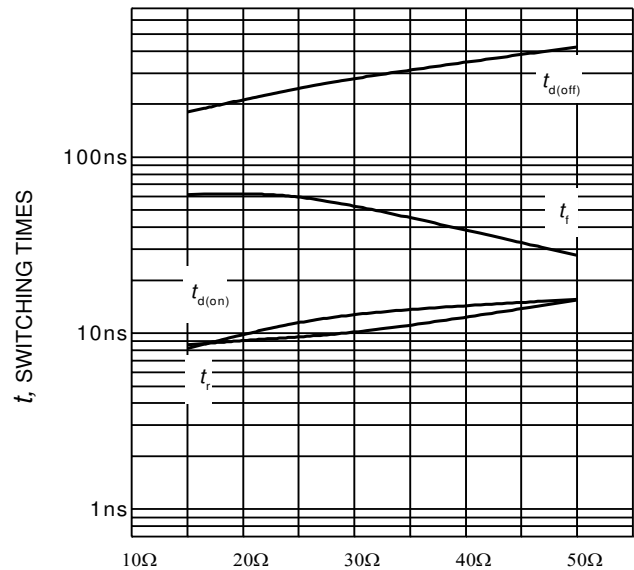


**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



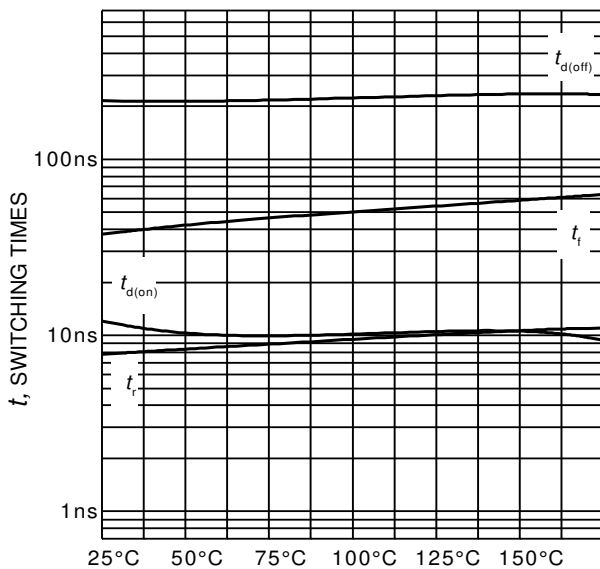
$I_C$ , COLLECTOR CURRENT

**Figure 9. Typical switching times as a function of collector current**  
(inductive load,  $T_J=175^\circ\text{C}$ ,  
 $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $r_G = 23\Omega$ ,  
Dynamic test circuit in Figure E)



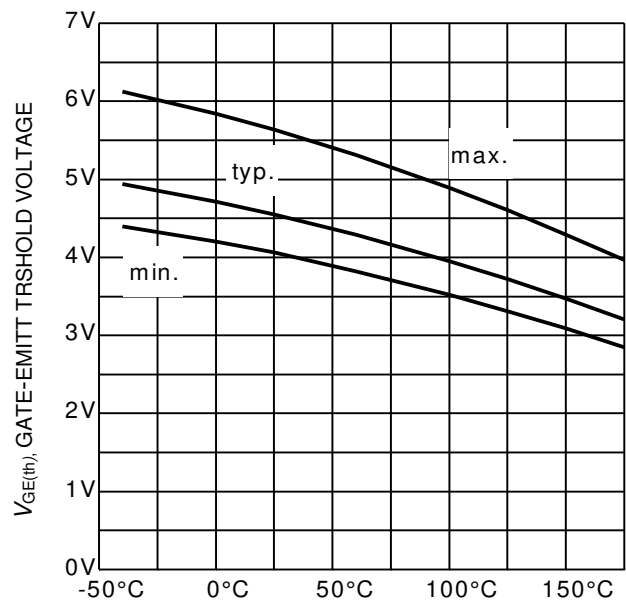
$R_G$ , GATE RESISTOR

**Figure 10. Typical switching times as a function of gate resistor**  
(inductive load,  $T_J = 175^\circ\text{C}$ ,  
 $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 10\text{A}$ ,  
Dynamic test circuit in Figure E)



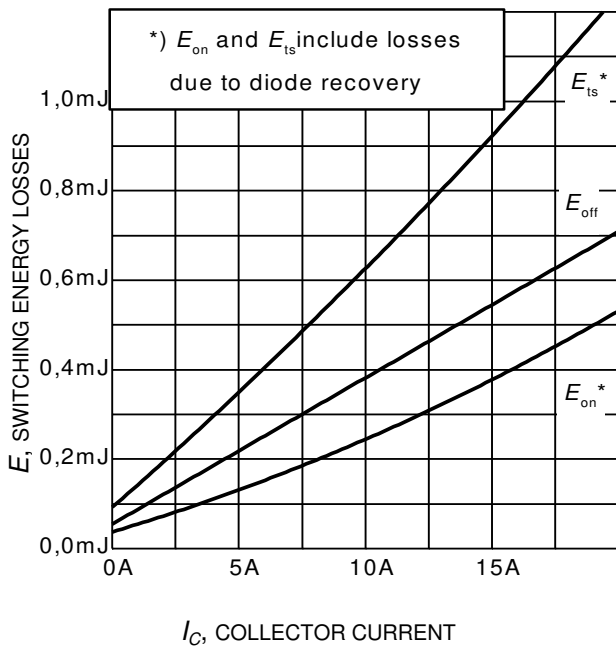
$T_J$ , JUNCTION TEMPERATURE

**Figure 11. Typical switching times as a function of junction temperature**  
(inductive load,  $V_{CE} = 400\text{V}$ ,  
 $V_{GE} = 0/15\text{V}$ ,  $I_C = 10\text{A}$ ,  $r_G=23\Omega$ ,  
Dynamic test circuit in Figure E)

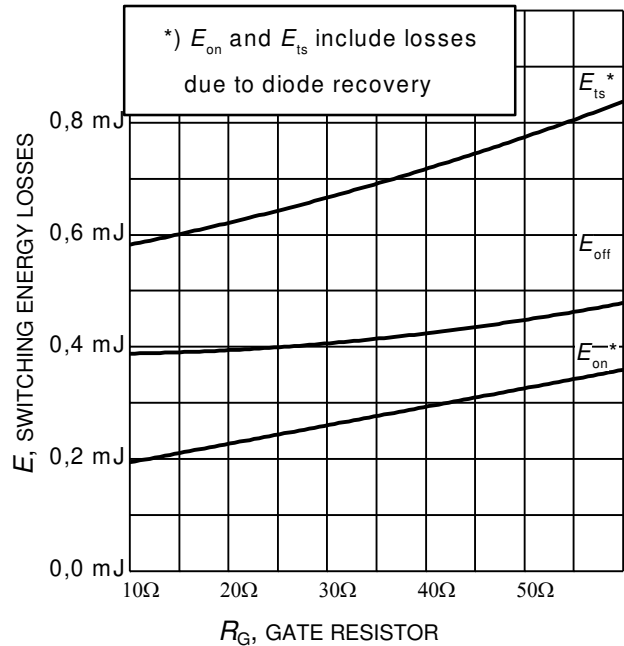


$T_J$ , JUNCTION TEMPERATURE

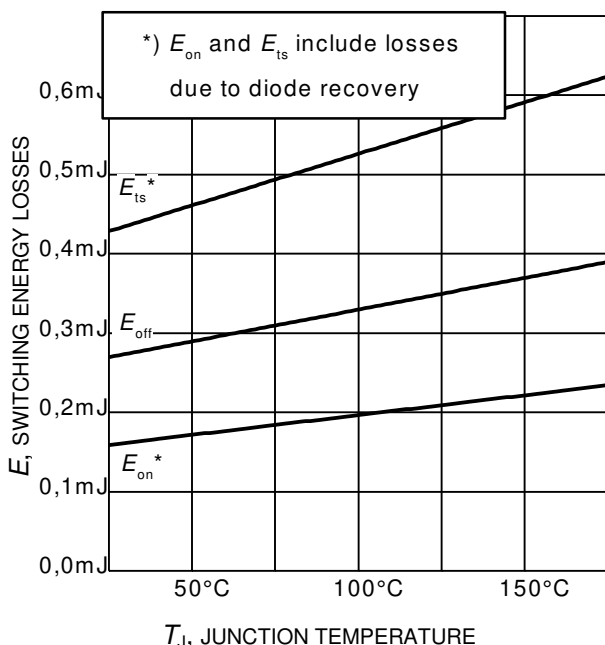
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
( $I_C = 0.3\text{mA}$ )



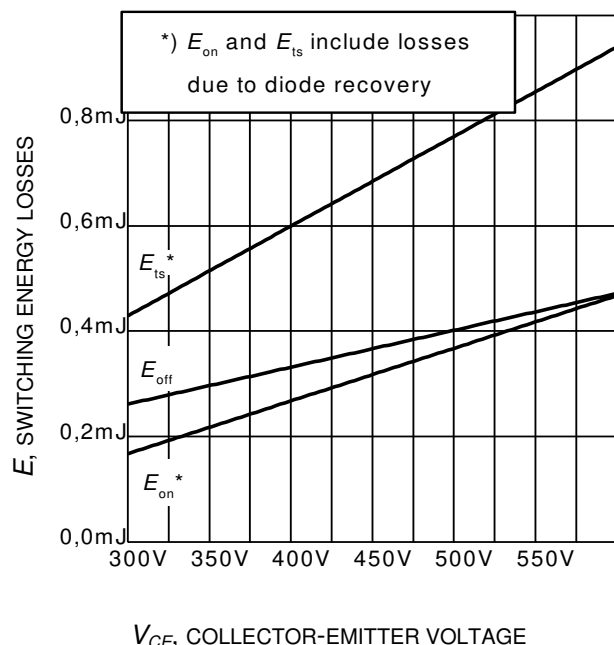
**Figure 13. Typical switching energy losses as a function of collector current**  
 (inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $r_G = 23\Omega$ , Dynamic test circuit in Figure E)



**Figure 14. Typical switching energy losses as a function of gate resistor**  
 (inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 10\text{A}$ , Dynamic test circuit in Figure E)

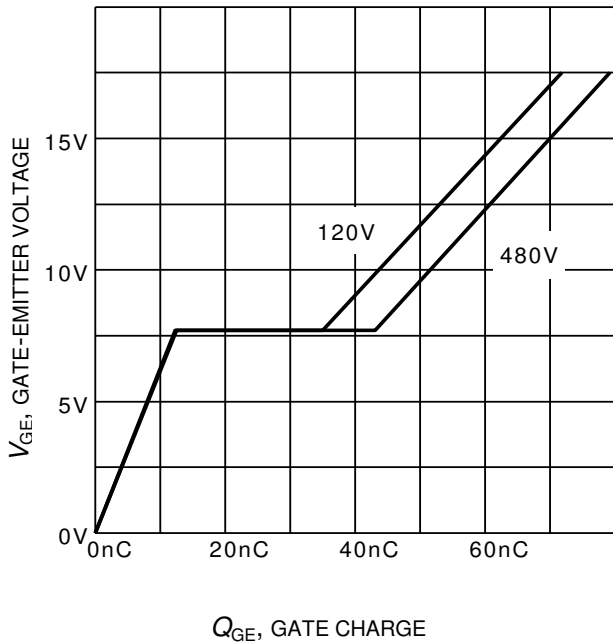


**Figure 15. Typical switching energy losses as a function of junction temperature**  
 (inductive load,  $V_{CE} = 400\text{V}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 10\text{A}$ ,  $r_G = 23\Omega$ , Dynamic test circuit in Figure E)

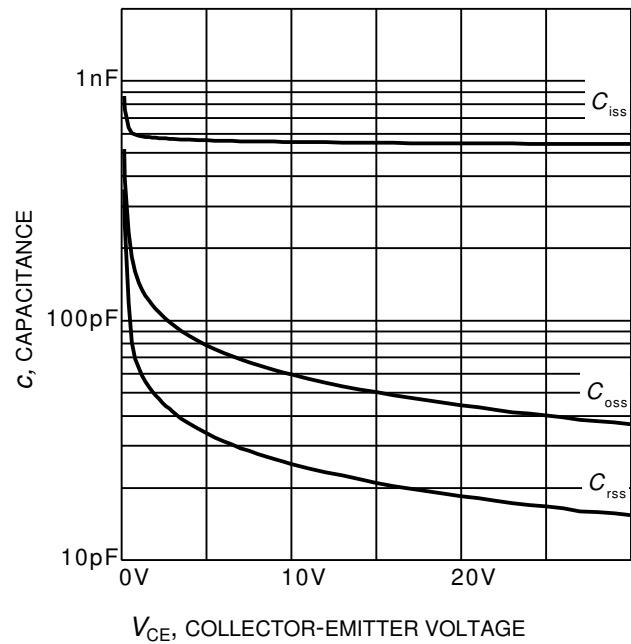


**Figure 16. Typical switching energy losses as a function of collector emitter voltage**  
 (inductive load,  $T_J = 175^\circ\text{C}$ ,  $V_{GE} = 0/15\text{V}$ ,  $I_C = 10\text{A}$ ,  $r_G = 23\Omega$ , Dynamic test circuit in Figure E)

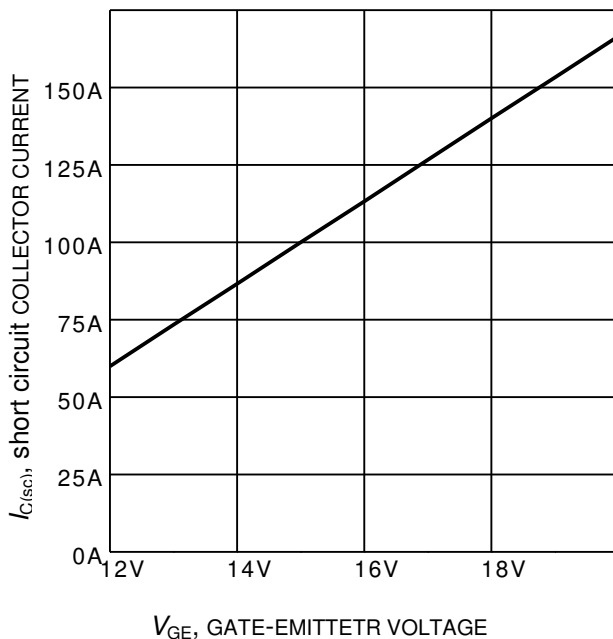




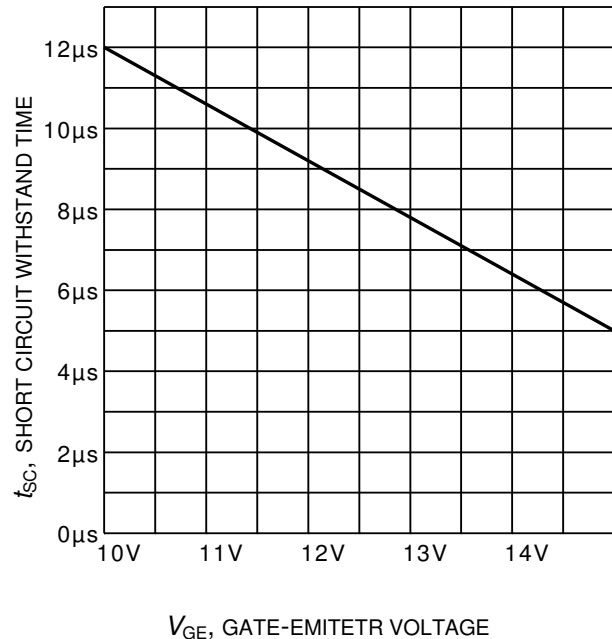
**Figure 17. Typical gate charge**  
( $I_C=10\text{ A}$ )



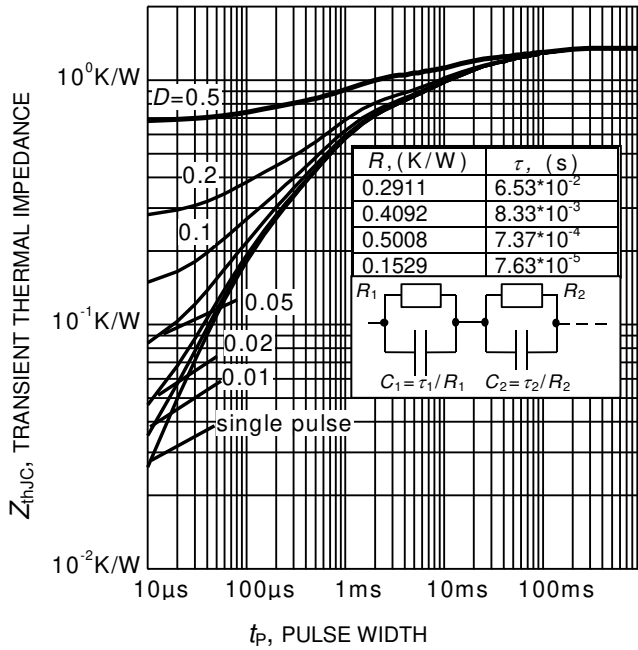
**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE}=0\text{V}$ ,  $f = 1\text{ MHz}$ )



**Figure 19. Typical short circuit collector current as a function of gate-emitter voltage**  
( $V_{CE} \leq 400\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )

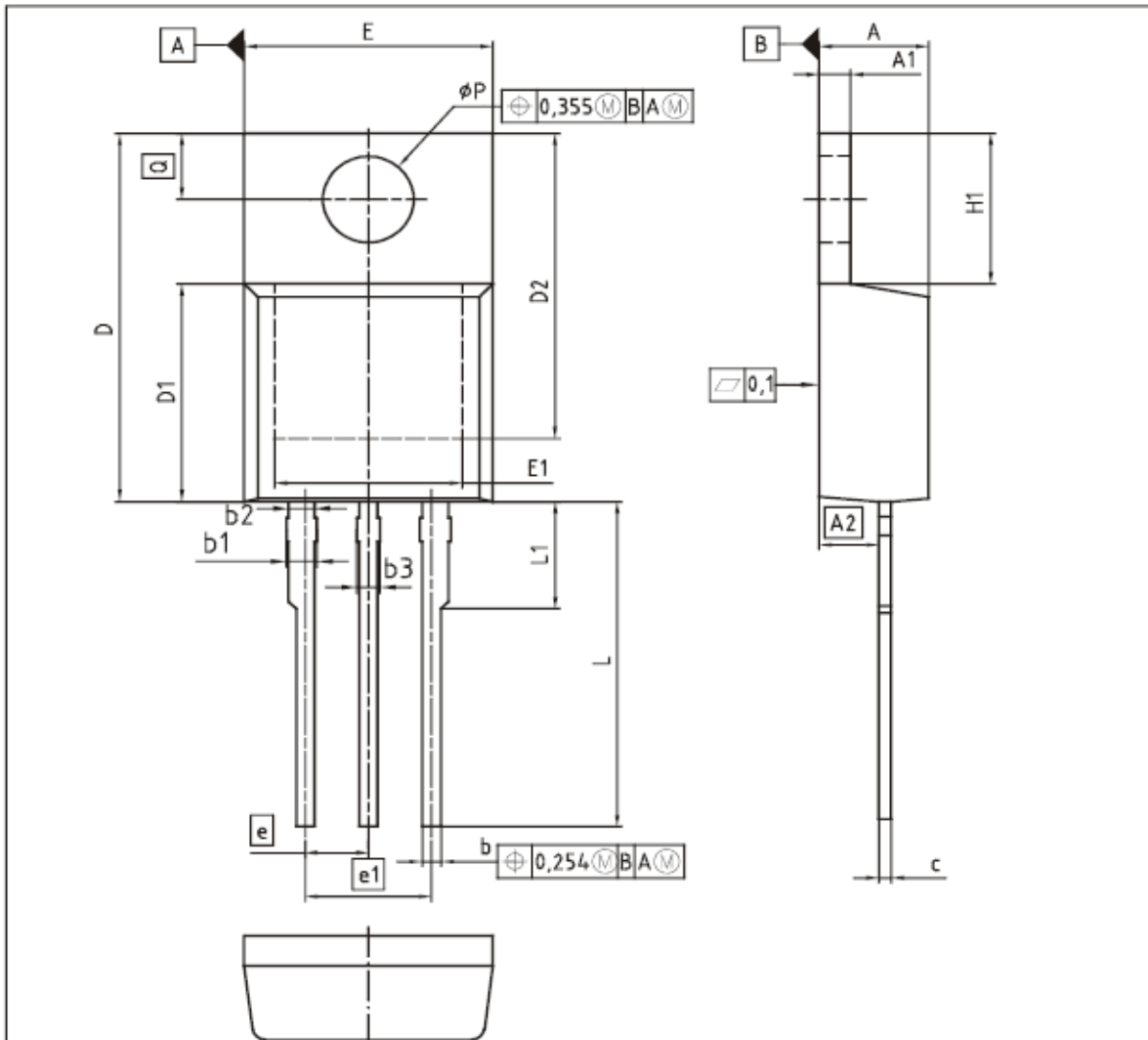


**Figure 20. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE}=400\text{V}$ , start at  $T_j=25^\circ\text{C}$ ,  $T_{jmax}<150^\circ\text{C}$ )



**Figure 21. IGBT transient thermal impedance**  
 $(D = t_p / T)$

### PG-TO220-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4,30	4,57	0,169	0,180
A1	1,17	1,40	0,046	0,055
A2	2,15	2,72	0,085	0,107
b	0,65	0,86	0,026	0,034
b1	0,95	1,40	0,037	0,055
b2	0,95	1,15	0,037	0,045
b3	0,65	1,15	0,026	0,045
c	0,33	0,60	0,013	0,024
D	14,81	15,95	0,583	0,628
D1	8,51	9,45	0,335	0,372
D2	12,19	13,10	0,480	0,516
E	9,70	10,36	0,382	0,408
E1	6,50	8,60	0,256	0,339
e	2,54		0,100	
e1	5,08		0,200	
N	3		3	
H1	5,90	6,90	0,232	0,272
L	13,00	14,00	0,512	0,551
L1	-	4,80	-	0,189
phi P	3,60	3,89	0,142	0,153
Q	2,60	3,00	0,102	0,118

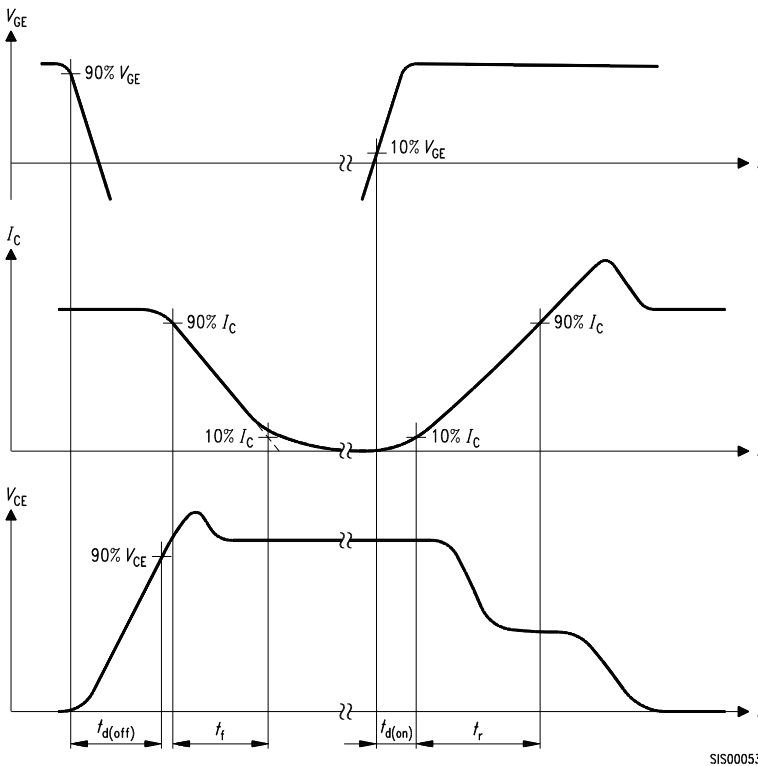
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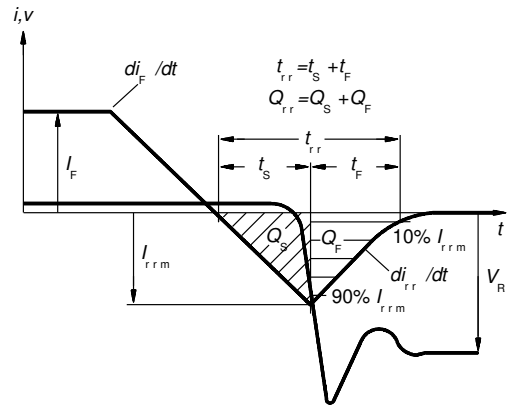
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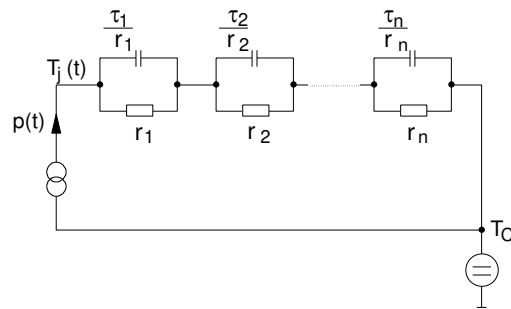
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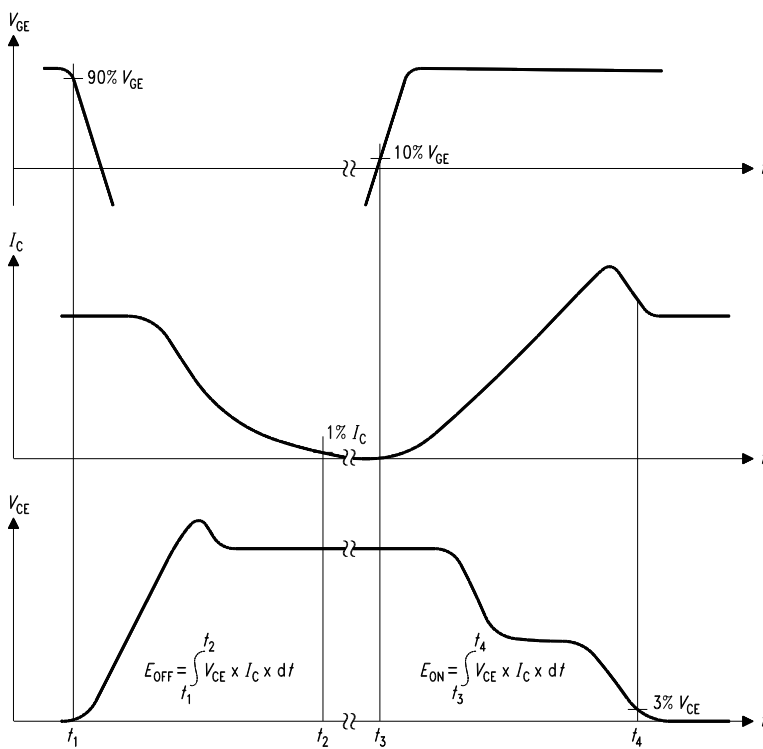
**Figure A. Definition of switching times**



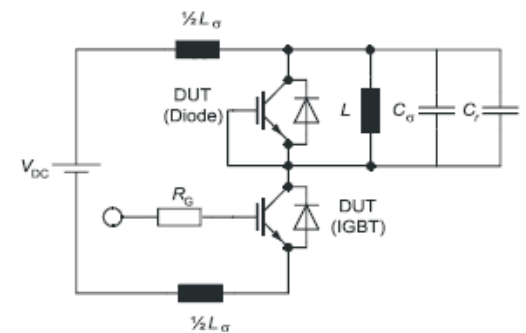
**Figure C. Definition of diodes switching characteristics**



**Figure D. Thermal equivalent circuit**



**Figure B. Definition of switching losses**



**Figure E. Dynamic test circuit**  
Parasitic inductance  $L_{\sigma}$ ,  
Parasitic capacitor  $C_{\sigma}$ ,  
Relief capacitor  $C_r$   
(only for ZVT switching)

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